Dr. Huichan Seo

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Huichan Seo, Ph.D. has been the Head of Etch Technology and the Program Leader of DRAM Front-End Patterning at SK Hynix for 5 years with responsibility for New Etching Gas Development, Simulation based Etching Technology Development and DRAM Front-End Patterning, which includes ISO STI, Buried Gate and High-k metal gate etching. Prior to joining SK Hynix, Seo was Senior Process Engineer at Intel. During his 10 years at Intel, Seo had responsibility for Tri-Gate Pattering, Fin Patterning and other Pathfinding Projects. He got 2 times IAA (Intel Achievement Award) for his great contribution on 3D transistor patterning and Device performance enhancement. Seo received a Ph.D. degree in Material Science and Engineering from University of Illinois at Urbana-Champaign, Champaign, IL, USA and Master/Bachelor degree in Material Science and Engineering from Seoul National University, Korea.